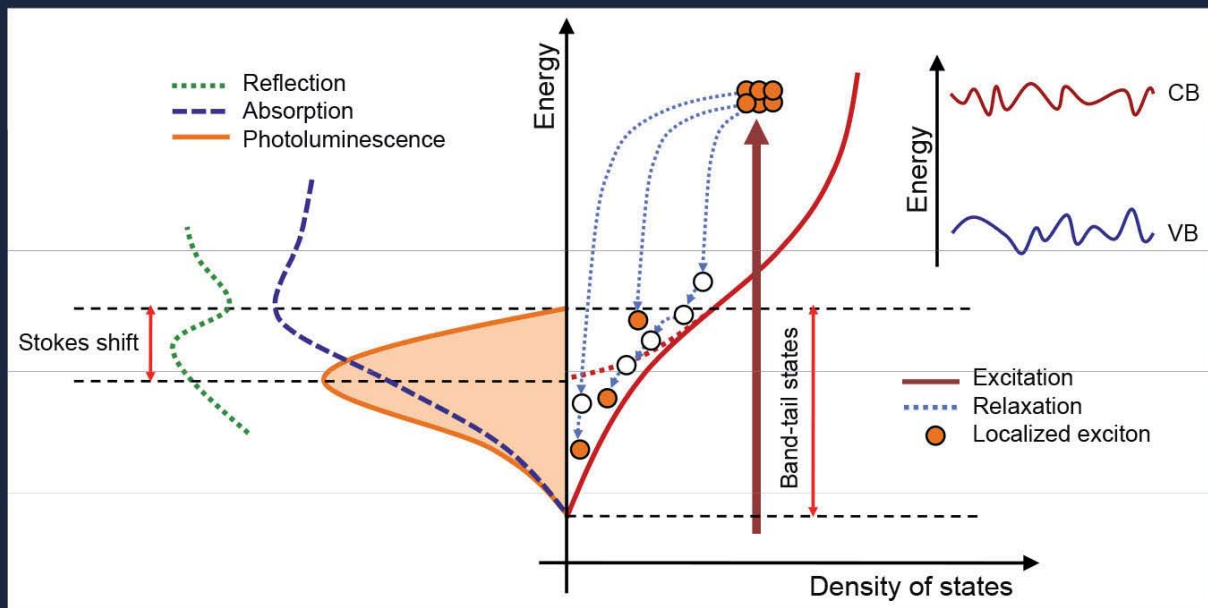


Localization Effects in Disordered III-V Semiconductor Nanostructures





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Der Fakultät für Elektrotechnik, Informationstechnik, Physik
der Technischen Universität Carolo-Wilhelmina zu Braunschweig

zur Erlangung des Grades eines Doktors

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1. Referent: Prof. Dr. rer. nat. Martin Koch

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Telefon: 0551-54724-0

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To my family

*Making a mistake is not a big deal as long as
you have learned from ...*



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Marburg, in June 2015

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